

650V N-CHANNEL ENHANCEMENT MODE POWER MOSFET

MAIN CHARACTERISTICS

I_D	12A
V_{DSS}	650V
R_{DS(on)-typ}(@V_{GS}=10V)	<0.74Ω(Type:0.59Ω)

FEATURES

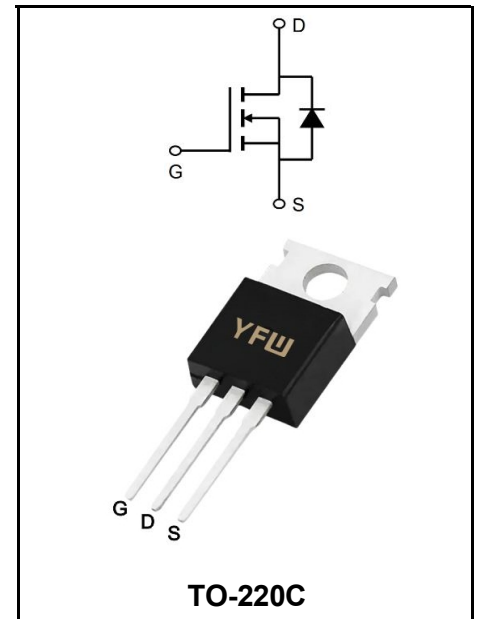
- ♦Fast Switching
- ♦Low ON Resistance
- ♦Low Gate Charge
- ♦100% Single Pulse avalanche energy Test

Application

- ♦Power switch circuit of adaptor and charger.

MECHANICAL DATA

- ♦Case: TO-220C/AC
- ♦Mounting Position: Any
- ♦Molded Plastic: UL Flammability Classification Rating 94V-0
- ♦Lead free in compliance with EU RoHS 2011/65/EU directive
- ♦Solder bath temperature 275℃ maximum,10s per JESD 22-B106



TO-220C

Maximum Ratings at Tc=25℃ unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	V
Continue Drain Current	I_D	12	A
Pulsed Drain Current (Note1)	I_{DM}	48	A
Power Dissipation	P_D	150	W
Single Pulse Avalanche Energy(Note2)	E_{AS}	750	mJ
Operating Temperature Range	T_J	150	℃
Storage Temperature Range	T_{STG}	-55 to +150	℃
Thermal Resistance, Junction to Case	R_{θJC}	0.83	℃/W
Thermal Resistance, Junction to Ambient	R_{θJA}	62.5	℃/W

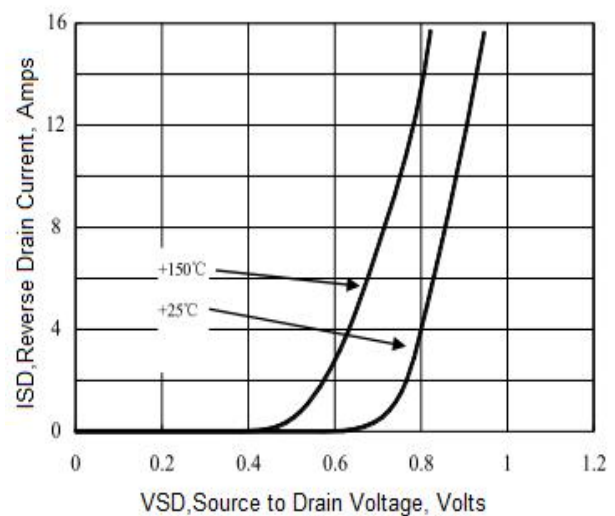
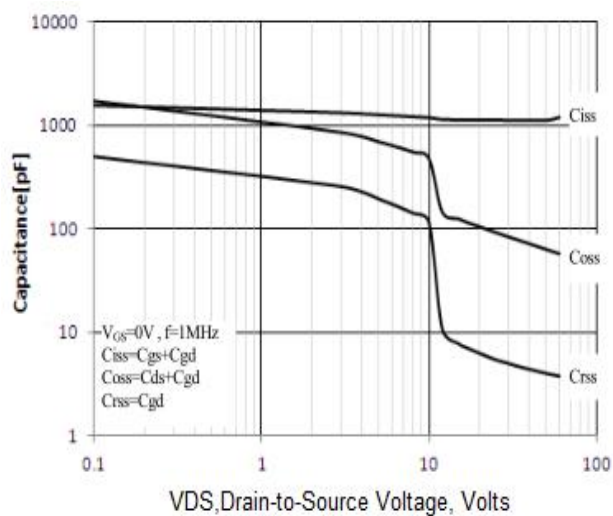
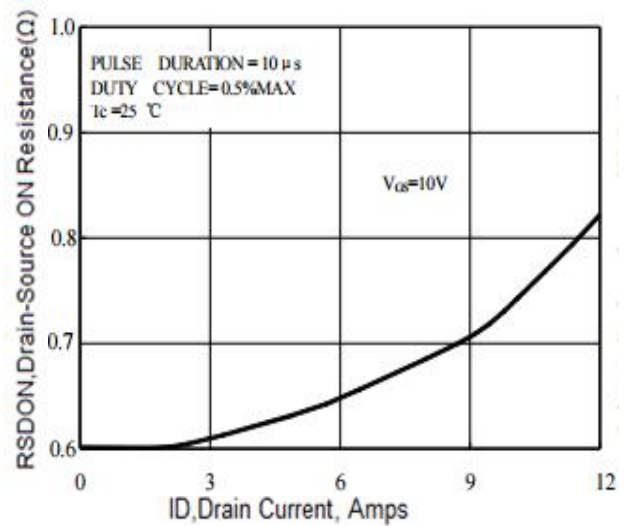
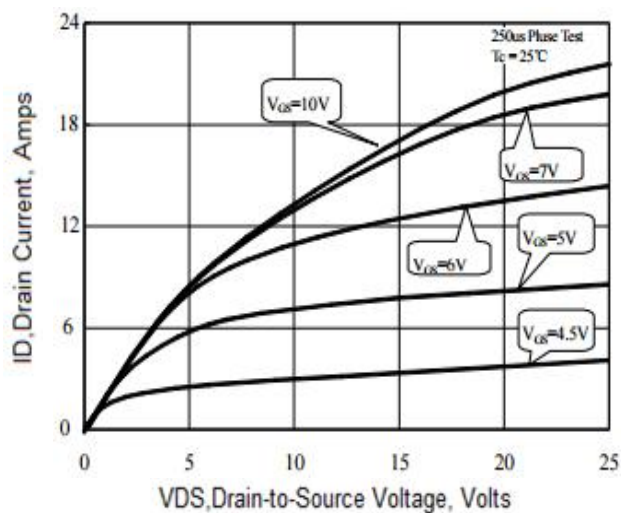
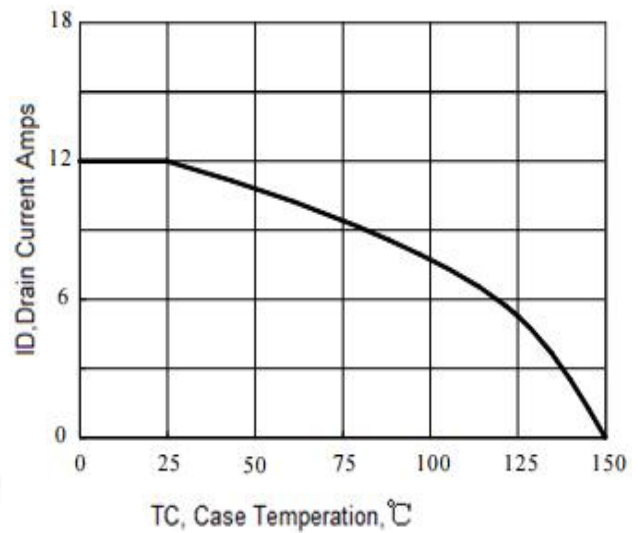
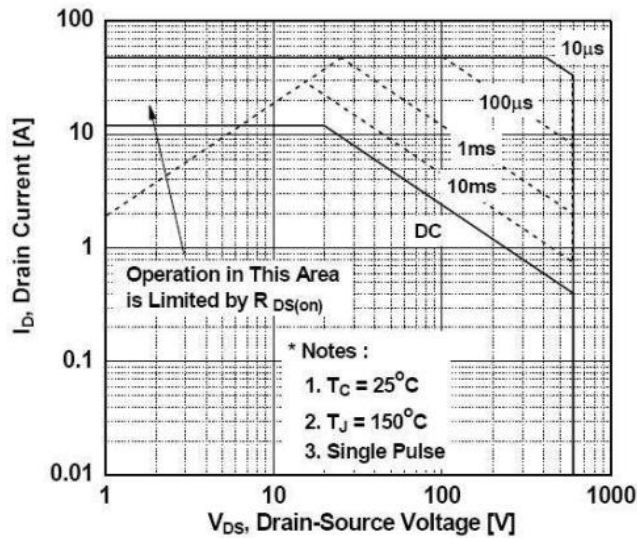
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

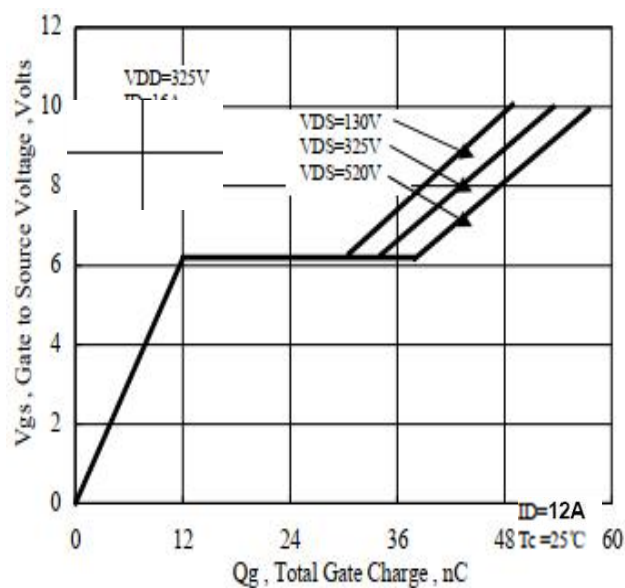
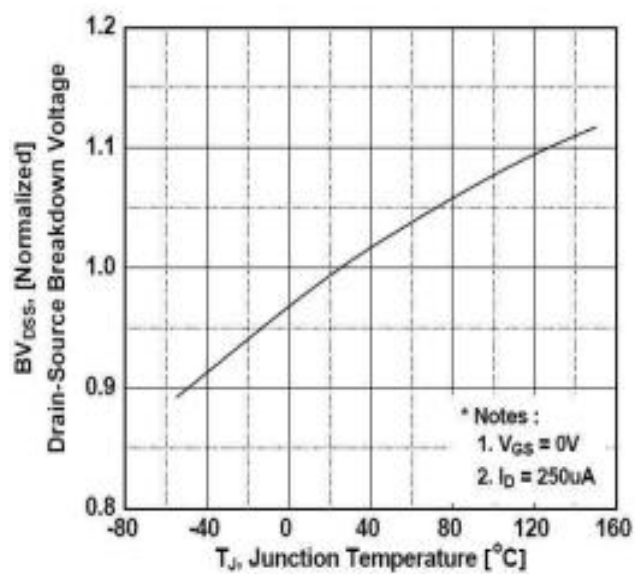
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	650	690	-	V
Drain-Source Leakage Current	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V}$	I_{DSS}	-	-	1	μA
	$V_{DS}=520\text{ V}, T_c=125^\circ\text{C}$		-	-	10	μA
Gate Leakage Current	$V_{GS}=\pm 30\text{ V}, V_{DS}=0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS}=10\text{ V}, I_D=6\text{ A}$	$R_{DS(ON)}$	-	0.59	0.74	Ω
Forward Transconductance	$V_{DS}=40\text{ V}, I_D=6\text{ A}$	g_{fs}	-	11	-	S
Input Capacitance	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f = 1\text{ MHz}$	C_{iss}	-	2450	-	pF
Output Capacitance		C_{oss}	-	140	-	
Reverse Transfer Capacitance		C_{rss}	-	9	-	
Turn-on Delay Time	$I_D = 12\text{ A}, V_{DD} = 325\text{ V},$ $R_G = 10\text{ }\Omega$	$t_{d(on)}$	-	29	-	ns
Rise Time		T_r	-	27	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	65	-	
Fall Time		t_f	-	46	-	
Total Gate Charge	$I_D = 12\text{ A}, V_{DD} = 520\text{ V},$ $V_{GS} = 10\text{ V}$	Q_g	-	50	-	nC
Gate to Source Charge		Q_{gs}	-	10	-	
Gate to Drain Charge		Q_{gd}	-	14	-	
Maximun Body-Diode Continuous Current		I_S	-	-	12	A
Maximun Body-Diode Pulsed Current		I_{SM}	-	-	48	A
Drain-Source Diode Forward Voltage	$I_{SD} = 12\text{ A}$	V_{SD}	-	-	1.5	V
Reverse Recovery Time	$I_{SD}=12\text{ A}, V_{GS}=0\text{ V},$	t_{rr}	-	670	-	ns
Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	4.4	-	μC

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

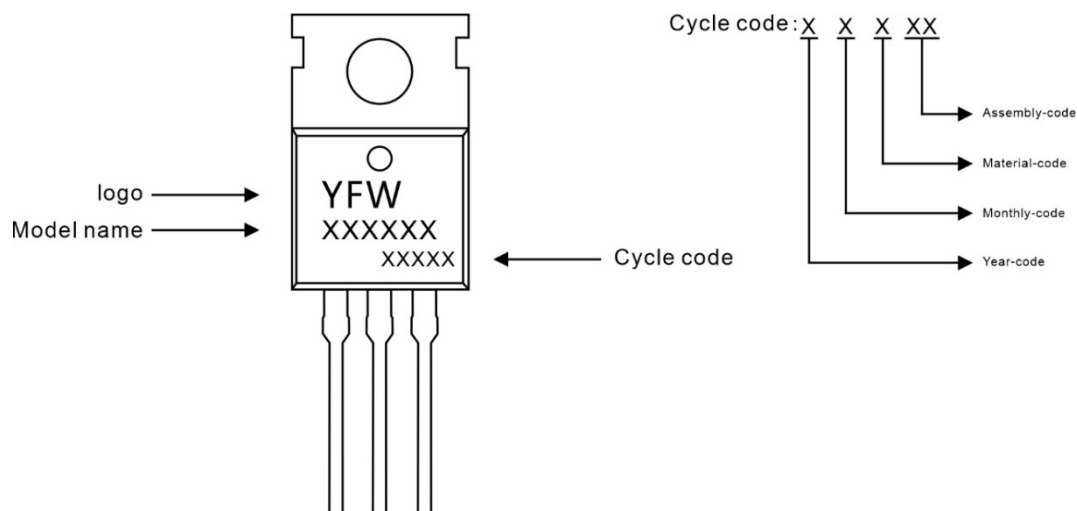
Ratings and Characteristic Curves



Ratings and Characteristic Curves



Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW12N65AC	TO-220C	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions

TO-220C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

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